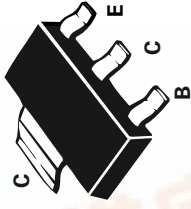


**SOT223 PNP SILICON PLANAR MEDIUM POWER  
HIGH PERFORMANCE TRANSISTOR**

ISSUE 2 - OCTOBER 1995

PARTMARKING DETAILS - FZT589  
COMPLEMENTARY TYPES - FZT489

**FZT589**



**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-2	A
Continuous Collector Current	$I_C$	-1	A
Base Current	$I_B$	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^{\circ}C$  unless otherwise stated)**

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50		V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30		V	$I_C = 1mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = 100\mu A$
Collector Cut-Off Current	$I_{CBO}$		-100	nA	$V_{CE} = 30V$
Collector Emitter Cut-Off Current	$I_{CES}$		-100	nA	$V_{CE} = 30V$
Emitter Cut-Off Current	$I_{EBO}$		-100	nA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-0.35		V	$I_C = 1A, I_B = 100mA^*$
		-0.65		V	$I_C = 2A, I_B = 200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.2	V	$I_C = 1A, I_B = 100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.1	V	$I_C = 1A, V_{CE} = 2V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100	300		$I_C = 1mA, V_{CE} = 2V^*$
		80			$I_C = 500mA, V_{CE} = 2V^*$
		40			$I_C = 1A, V_{CE} = 2V^*$
					$I_C = 2A, V_{CE} = 2V^*$
Transition Frequency	$f_T$	100		MHz	$I_C = 100mA, V_{CE} = 5V$ $f = 100MHz$
Output Capacitance	$C_{ob0}$		15	pF	$V_{CE} = 10V, f = 1MHz$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$   
For typical characteristics graphs see FMMT549 datasheet

查询FZT589供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

